

RF LDMOS Wideband Integrated Power Amplifier

The MHV5IC1810N wideband integrated circuit is designed with on-chip matching that makes it usable from 1805 to 1990 MHz. This multi-stage structure is rated for 24 to 32 Volt operation and covers all typical cellular base station modulation formats.

Final Application

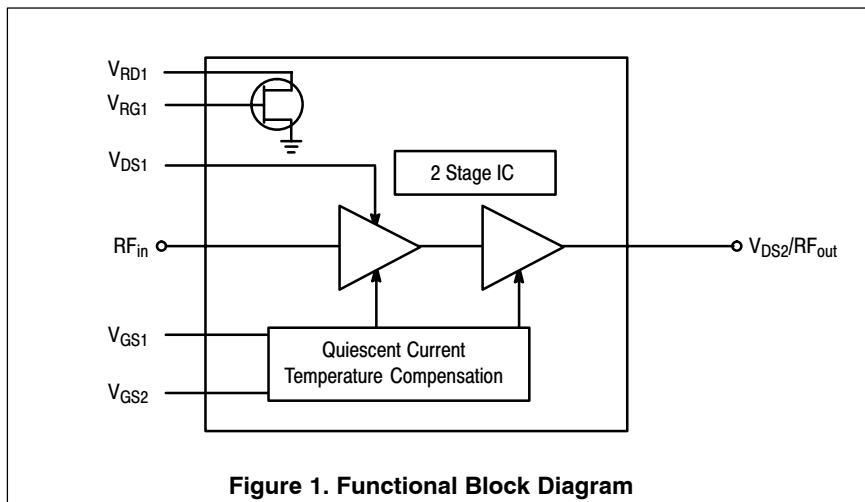
- Typical Two-Tone Performance: $V_{DD} = 28$ Volts, $I_{DQ1} = 120$ mA, $I_{DQ2} = 90$ mA, $P_{out} = 5$ Watts Avg., Full Frequency Band (1805-1880 MHz or 1930-1990 MHz)
Power Gain — 29 dB
Power Added Efficiency — 29%
IMD — -34 dBc

Driver Application

- Typical GSM EDGE Performance: $V_{DD} = 28$ Volts, $I_{DQ1} = 105$ mA, $I_{DQ2} = 95$ mA, $P_{out} = 35$ dBm, Full Frequency Band (1805-1880 MHz or 1930-1990 MHz)
Power Gain — 29 dB
Spectral Regrowth @ 400 kHz Offset = -67 dBc
Spectral Regrowth @ 600 kHz Offset = -76 dBc
EVM — 1.1% rms
- Capable of Handling 3:1 VSWR, @ 28 Vdc, 1990 MHz, 10 Watts CW Output Power
- Stable into a 3:1 VSWR. All Spurs Below -60 dBc @ 100 mW to 10 W CW P_{out} .

Features

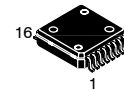
- Characterized with Series Equivalent Large-Signal Impedance Parameters and Common Source Scattering Parameters www.DataSheet4U.com
- On-Chip Matching (50 Ohm Input, >5 Ohm Output)
- Integrated Quiescent Current Temperature Compensation with Enable/Disable Function
- On-Chip Current Mirror g_m Reference FET for Self Biasing Application ⁽¹⁾
- Integrated ESD Protection
- RoHS Compliant
- In Tape and Reel. R2 Suffix = 1500 Units per 16 mm, 13 inch Reel.



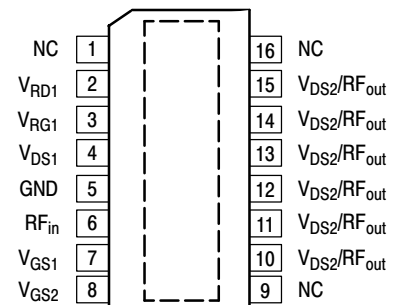
1. Refer to AN1987, *Quiescent Current Control for the RF Integrated Circuit Device Family*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1987.

MHV5IC1810NR2

**1805-1990 MHz, 5 W AVG., 28 V
GSM/GSM EDGE
RF LDMOS WIDEBAND
INTEGRATED POWER AMPLIFIER**



**CASE 978-03
PFP-16
PLASTIC**



(Top View)

Note: Exposed backside flag is source terminal for transistors.

Figure 2. Pin Connections

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +12	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Operating Junction Temperature	T_J	150	°C
Input Power	P_{in}	12	dBm

Table 2. Thermal Characteristics

Characteristic	Symbol	Value ⁽¹⁾	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		°C/W
Final Application ($P_{out} = 10$ W CW)	Stage 1, 28 Vdc, $I_{DQ1} = 120$ mA Stage 2, 28 Vdc, $I_{DQ2} = 90$ mA	9.2 3.3	
Driver Application ($P_{out} = 2.25$ W CW)	Stage 1, 28 Vdc, $I_{DQ1} = 120$ mA Stage 2, 28 Vdc, $I_{DQ2} = 90$ mA	10 3.5	

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	0 (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	III (Minimum)

Table 4. Moisture Sensitivity Level

Test Methodology	Rating	Package Peak Temperature	Unit
Per JESD 22-A113, IPC/JEDEC J-STD-020	3	260	°C

Table 5. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

Functional Tests (In Freescale Wideband 1930-1990 MHz Test Fixture, 50 ohm system) $V_{DD} = 28$ Vdc, $I_{DQ1} = 120$ mA, $I_{DQ2} = 90$ mA, $P_{out} = 5$ W Avg., $f_1 = 1990$ MHz, $f_2 = 1990.1$ MHz, Two-Tone Test

Power Gain	G_{ps}	26.5	29	—	dB
Power Added Efficiency	PAE	25	29	—	%
Intermodulation Distortion	IMD	—	-34	-27	dBc
Input Return Loss	IRL	—	—	-10	dB

Typical Two-Tone Performances (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28$ Vdc, $I_{DQ1} = 120$ mA, $I_{DQ2} = 90$ mA, $P_{out} = 5$ W Avg., 1805-1880 MHz

Power Gain	G_{ps}	—	29	—	dB
Power Added Efficiency	PAE	—	29	—	%
Intermodulation Distortion	IMD	—	-34	—	dBc
Input Return Loss	IRL	—	-15	—	dB

Typical GSM EDGE Performances (In Freescale GSM EDGE Test Fixture, 50 ohm system) $V_{DD} = 28$ Vdc, $I_{DQ1} = 105$ mA, $I_{DQ2} = 95$ mA, $P_{out} = 3.2$ W Avg., 1805-1880 MHz or 1930-1990 MHz EDGE Modulation

Power Gain	G_{ps}	—	29	—	dB
Error Vector Magnitude	EVM	—	1.1	—	% rms
Spectral Regrowth at 400 kHz Offset	SR1	—	-67	—	dBc
Spectral Regrowth at 600 kHz Offset	SR2	—	-76	—	dBc

1. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>.
Select Documentation/Application Notes - AN1955.

Table 5. Electrical Characteristics — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted) **(continued)**

Characteristic	Symbol	Min	Typ	Max	Unit
Typical CW Performances (In Freescale CW Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ1} = 120\text{ mA}$, $I_{DQ2} = 90\text{ mA}$, $P_{out} = 2.25\text{ W Avg.}$, 1805-1990 MHz					
Power Gain	G_{ps}	—	29	—	dB
Power Added Efficiency	PAE	—	19	—	%
Input Return Loss	IRL	—	-13	—	dB

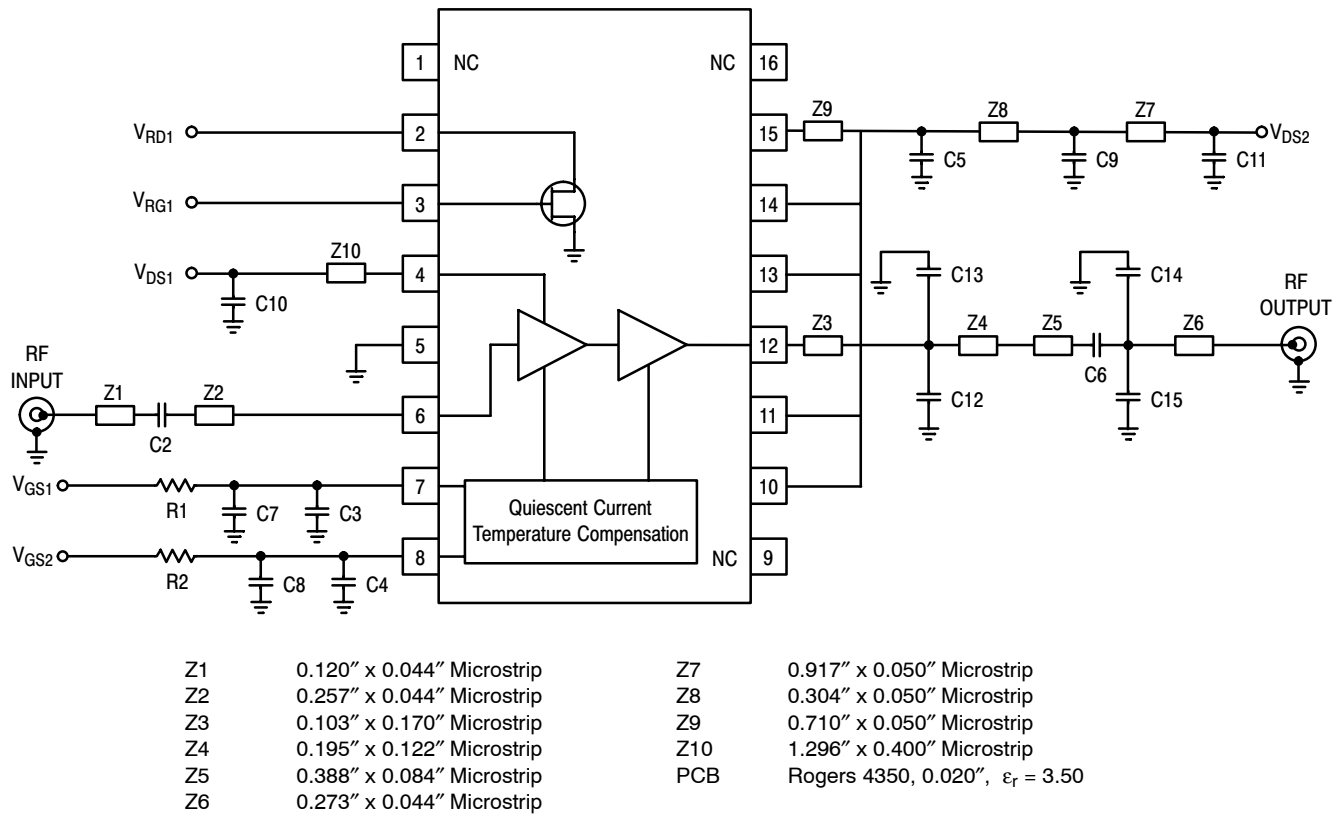


Figure 3. MHV5IC1810NR2 Test Circuit Schematic — 1930-1990 MHz

Table 6. MHV5IC1810NR2 Test Circuit Component Designations and Values — 1930-1990 MHz

Part	Description	Part Number	Manufacturer
C2	22 pF 100A Chip Capacitor	100A220GWT	ATC
C3, C4, C5, C6	8.2 pF 100A Chip Capacitors	100A8R2CW	ATC
C7, C8, C9	10 nF Chip Capacitors (0805)	08055C103KAT	AVX
C10, C11	6.8 μ F Chip Capacitors (1812)	C4532X5R1H685MT	TDK
C12, C13	3.3 pF 100A Chip Capacitors	100A3R3BW	ATC
C14, C15	0.5 pF 100A Chip Capacitors	100A0R5BW	ATC
R1, R2	1 k Ω , 1/8 W Chip Resistors (0805)		

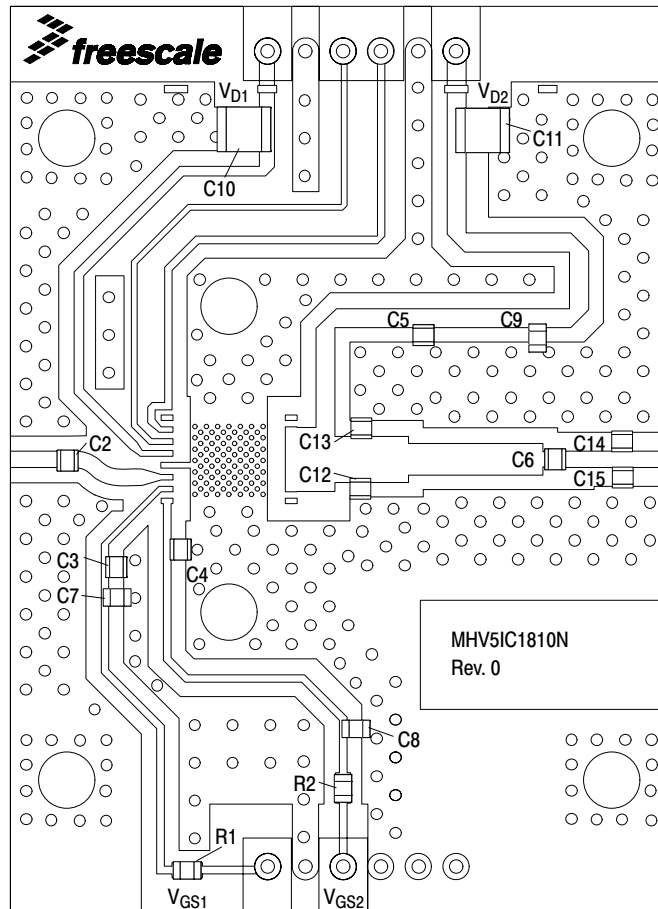
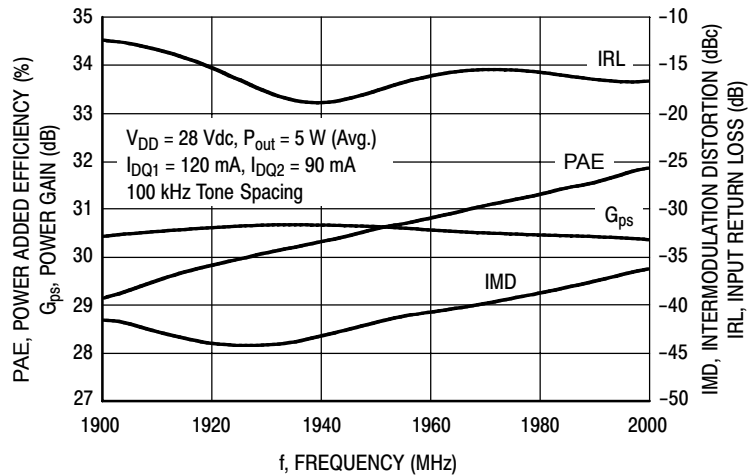
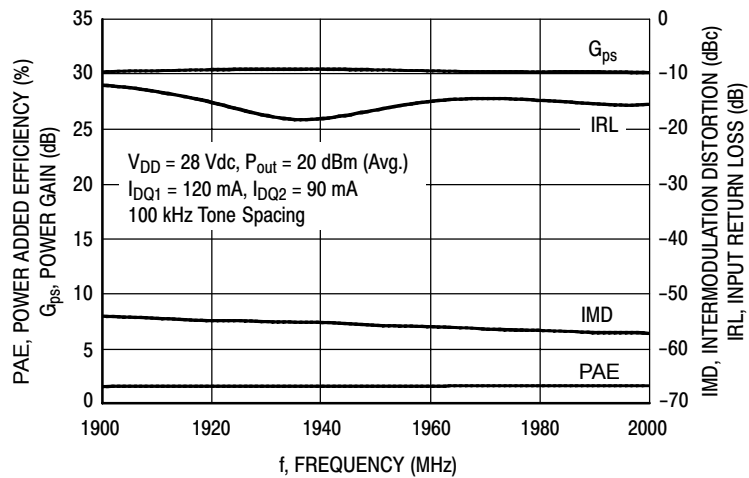


Figure 4. MHV5IC1810NR2 Test Circuit Component Layout — 1930-1990 MHz

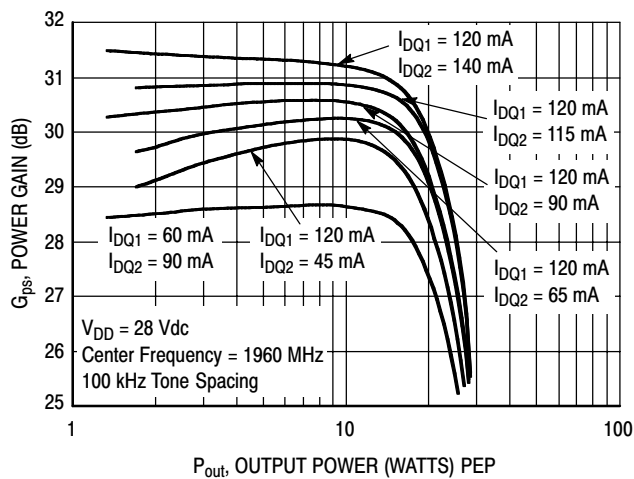
TYPICAL CHARACTERISTICS — 1930-1990 MHz



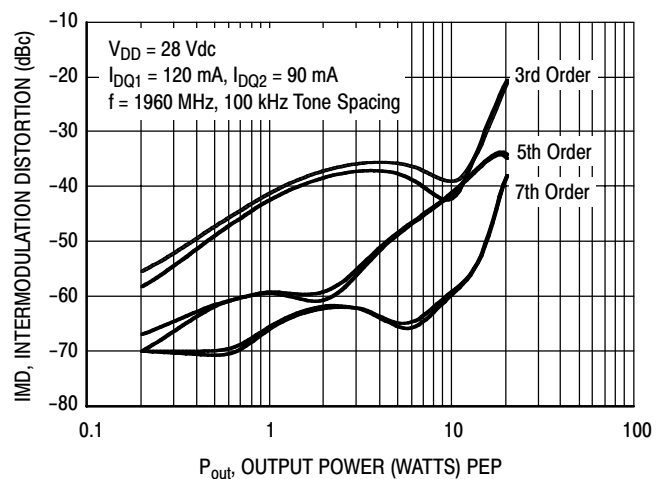
**Figure 5. Two-Tone Wideband Performance
@ $P_{out} = 5$ Watts (Avg.)**



**Figure 6. Two-Tone Wideband Performance
@ $P_{out} = 20$ dBm (Avg.)**



**Figure 7. Two-Tone Power Gain versus
Output Power**



**Figure 8. Intermodulation Distortion Products
versus Output Power**

TYPICAL CHARACTERISTICS — 1930-1990 MHz

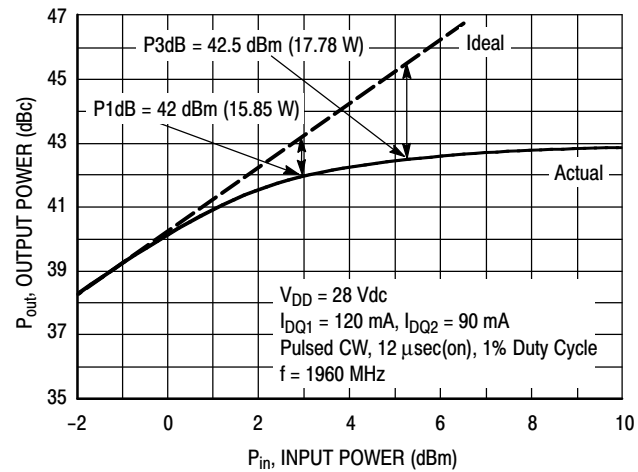


Figure 9. Pulse CW Output Power versus Input Power

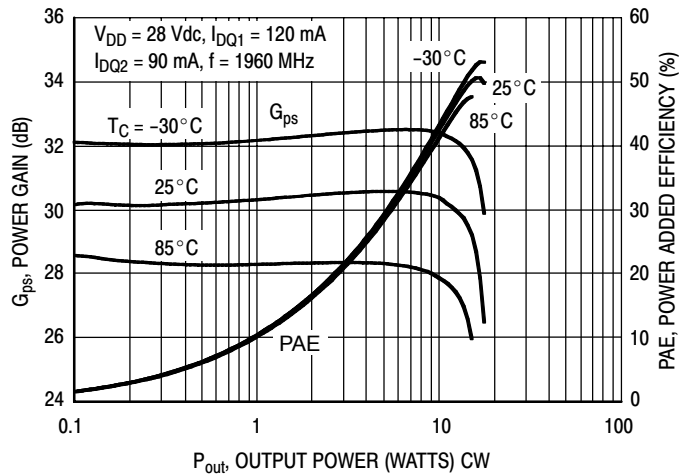


Figure 10. Power Gain and Power Added Efficiency versus CW Output Power

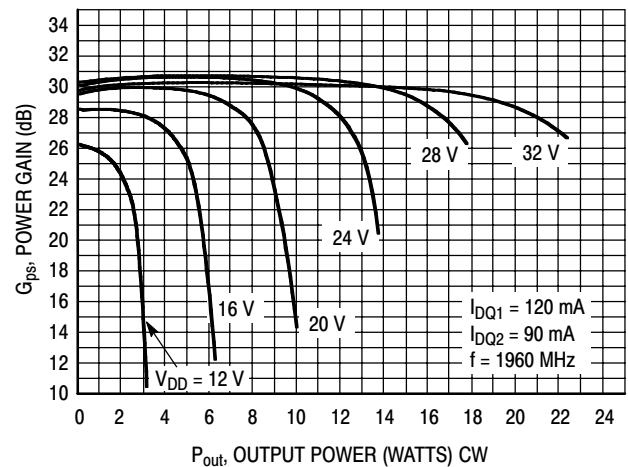


Figure 11. Power Gain versus Output Power

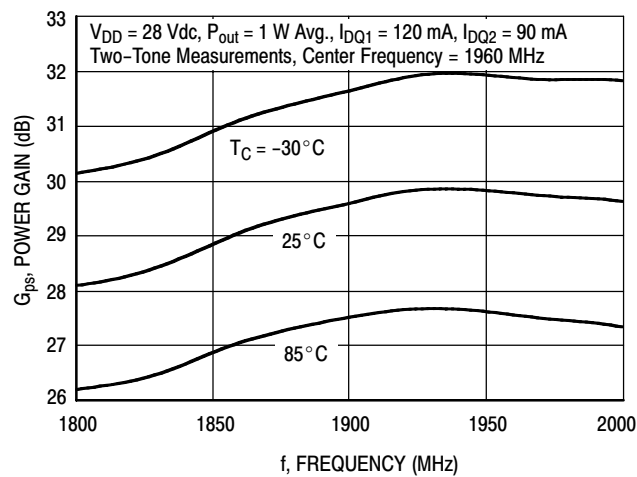


Figure 12. Power Gain versus Frequency

TYPICAL CHARACTERISTICS — 1930-1990 MHz

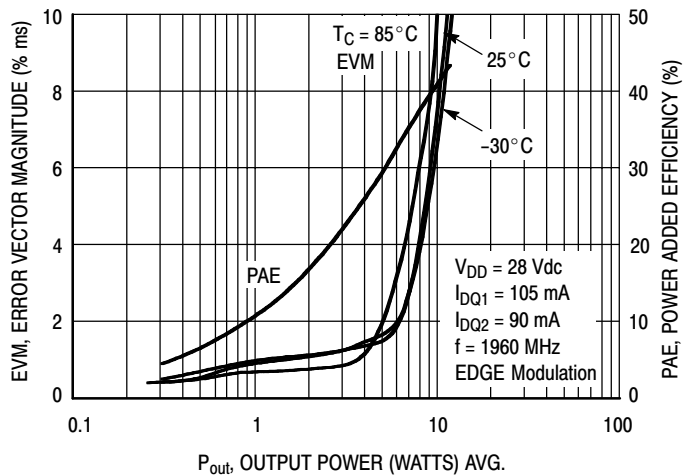


Figure 13. EVM and Power Added Efficiency versus Output Power

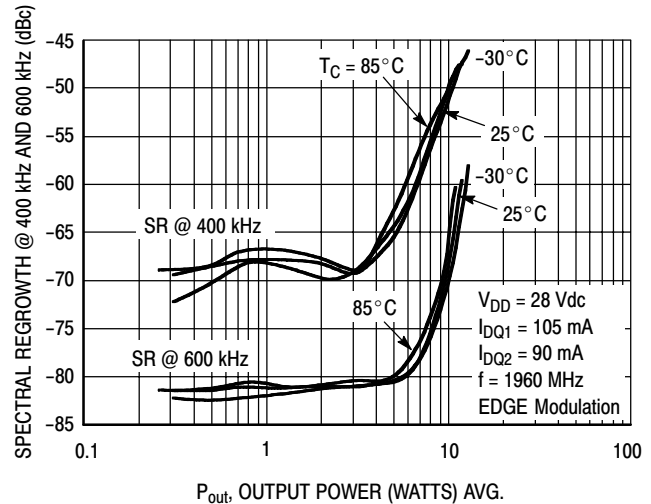
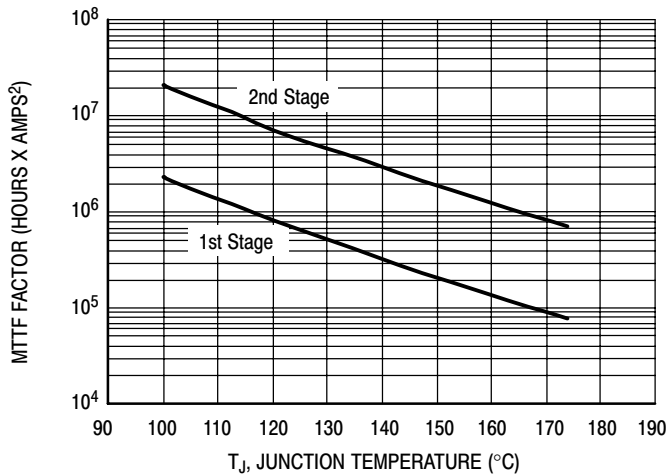


Figure 14. Spectral Regrowth at 400 and 600 kHz versus Output Power



This above graph displays calculated MTTF in hours x ampere² drain current. Life tests at elevated temperatures have correlated to better than $\pm 10\%$ of the theoretical prediction for metal failure. Divide MTTF factor by I_D^2 for MTTF in a particular application.

Figure 15. MTTF Factor versus Junction Temperature

GSM TEST SIGNAL

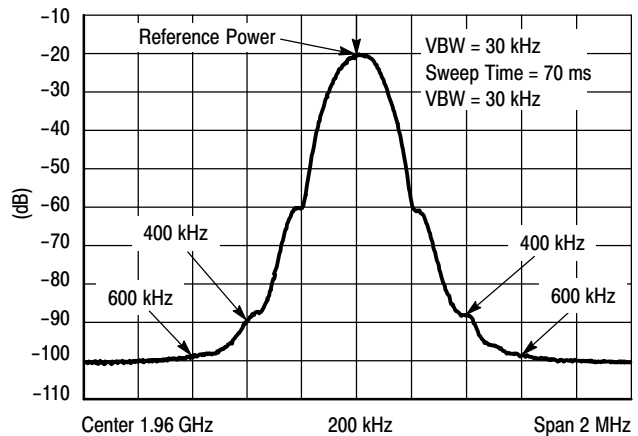


Figure 16. EDGE Spectrum

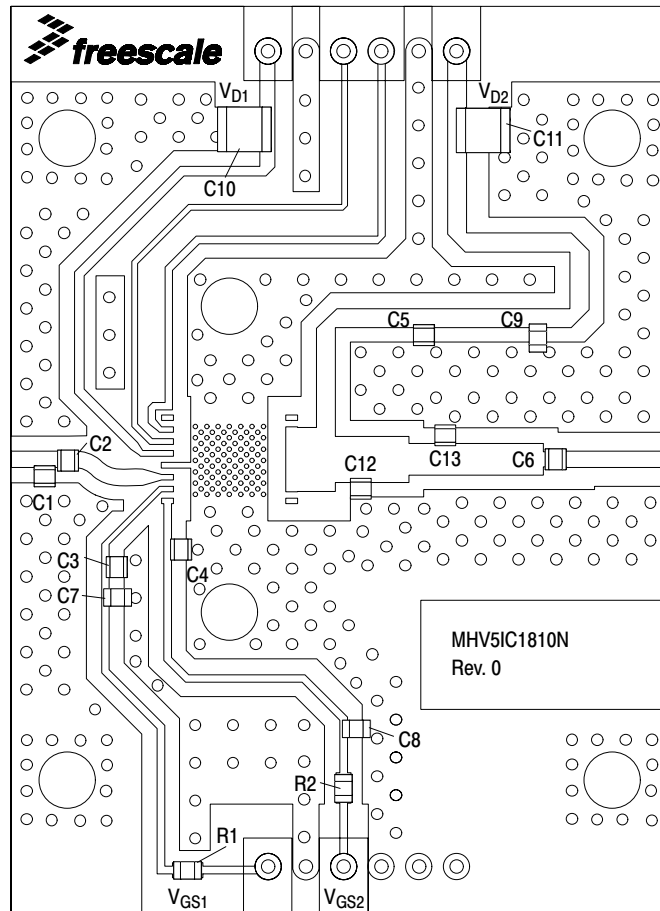


Figure 18. MHV5IC1810NR2 Test Circuit Component Layout — 1805-1880 MHz

TYPICAL CHARACTERISTICS — 1805-1880 MHz

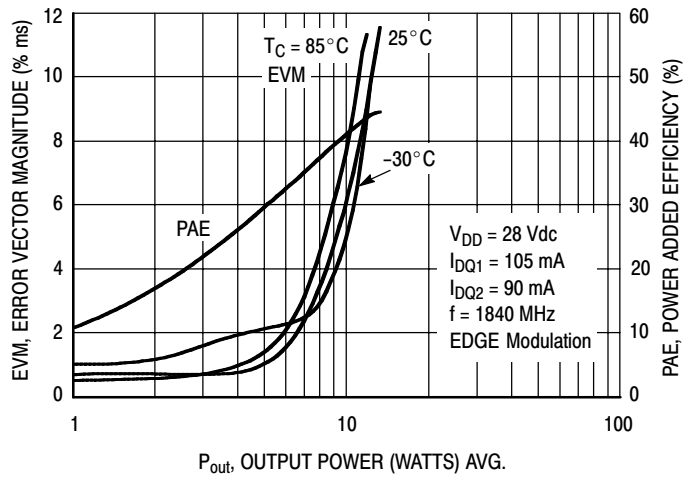


Figure 19. Spectral Regrowth at 400 and 600 kHz versus Output Power

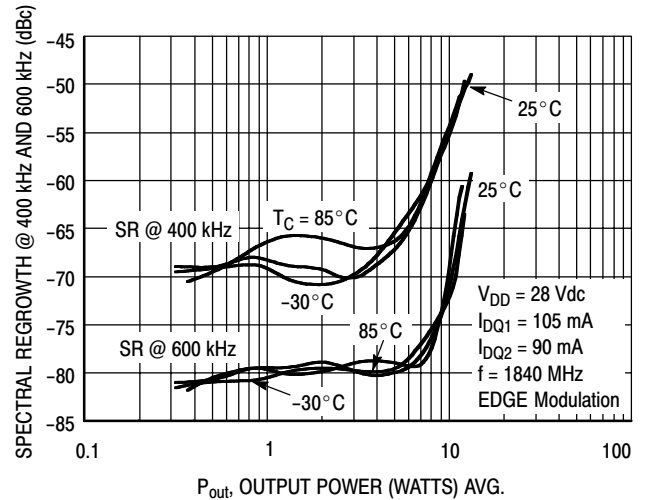
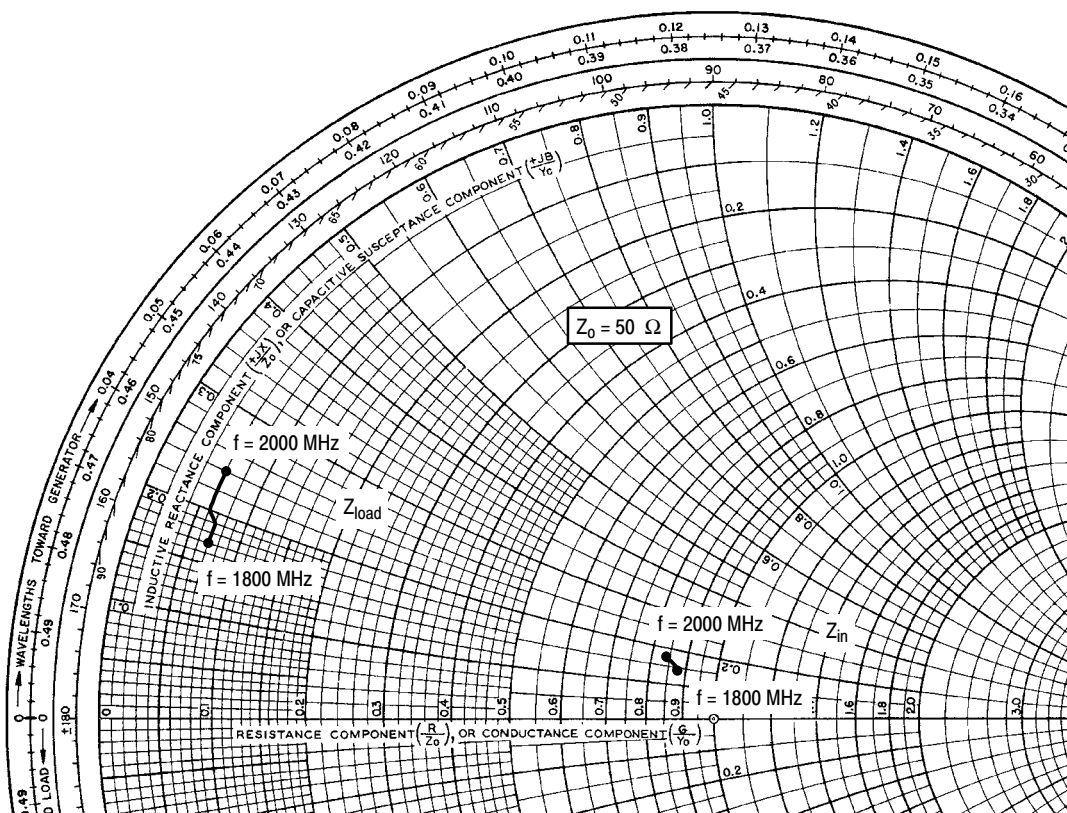


Figure 20. Spectral Regrowth at 400 and 600 kHz versus Output Power



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ1} = 120 \text{ mA}$, $I_{DQ2} = 90 \text{ mA}$, $P_{out} = 5 \text{ W Avg.}$

f MHz	Z_{in} Ω	Z_{load} Ω
1800	$43.82 + j6.83$	$3.49 + j8.58$
1820	$43.67 + j7.10$	$3.43 + j8.96$
1840	$43.50 + j7.34$	$3.36 + j9.33$
1860	$43.31 + j7.55$	$3.31 + j9.68$
1880	$43.13 + j7.76$	$3.24 + j10.04$
1900	$42.96 + j7.96$	$3.19 + j10.38$
1920	$42.76 + j8.15$	$3.14 + j10.72$
1940	$42.56 + j8.34$	$3.07 + j11.03$
1960	$42.36 + j8.50$	$3.04 + j11.36$
1980	$42.16 + j8.65$	$2.99 + j11.65$
2000	$41.97 + j8.79$	$2.94 + j11.94$

Z_{in} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

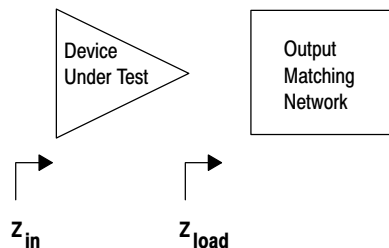
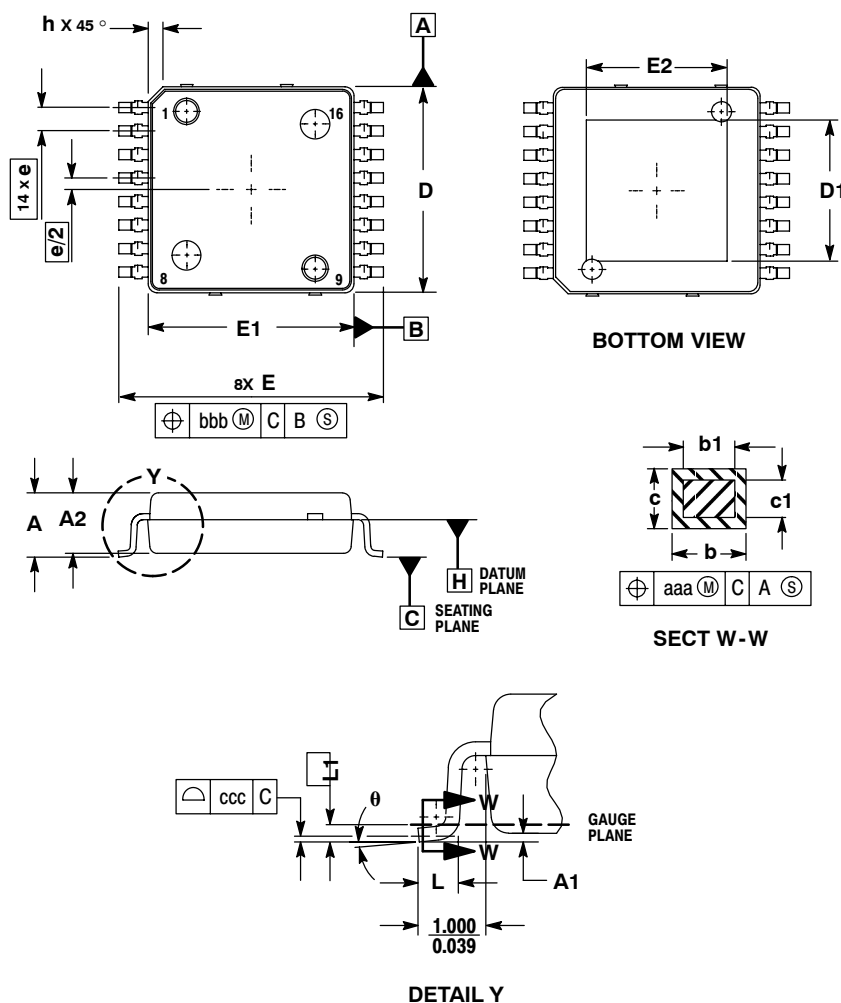


Figure 21. Series Equivalent Input and Load Impedance

NOTES

NOTES

PACKAGE DIMENSIONS



NOTES:

1. CONTROLLING DIMENSION: MILLIMETER.
2. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DATUM PLANE -H- IS LOCATED AT BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE BOTTOM OF THE PARTING LINE.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.250 PER SIDE. DIMENSIONS D AND E1 DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
5. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS 0.127 TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. DATUMS -A- AND -B- TO BE DETERMINED AT DATUM PLANE -H-.

DIM	MILLIMETERS	
	MIN	MAX
A	2.000	2.300
A1	0.025	0.100
A2	1.950	2.100
D	6.950	7.100
D1	4.372	5.180
E	8.850	9.150
E1	6.950	7.100
E2	4.372	5.180
L	0.466	0.720
L1	0.250 BSC	
b	0.300	0.432
b1	0.300	0.375
c	0.180	0.279
c1	0.180	0.230
e	0.800 BSC	
h	---	0.600
θ	0°	7°
aaa	0.200	
bbb	0.200	
ccc	0.100	

**CASE 978-03
ISSUE C
PFP-16
PLASTIC**

How to Reach Us:

Home Page:
www.freescale.com

E-mail:
support@freescale.com

USA/Europe or Locations Not Listed:
Freescale Semiconductor
Technical Information Center, CH370
1300 N. Alma School Road
Chandler, Arizona 85224
+1-800-521-6274 or +1-480-768-2130
support@freescale.com

Europe, Middle East, and Africa:
Freescale Halbleiter Deutschland GmbH
Technical Information Center
Schatzbogen 7
81829 Muenchen, Germany
+44 1296 380 456 (English)
+46 8 52200080 (English)
+49 89 92103 559 (German)
+33 1 69 35 48 48 (French)
support@freescale.com

Japan:
Freescale Semiconductor Japan Ltd.
Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku,
Tokyo 153-0064
Japan
0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:
Freescale Semiconductor Hong Kong Ltd.
Technical Information Center
2 Dai King Street
Tai Po Industrial Estate
Tai Po, N.T., Hong Kong
+800 2666 8080
support.asia@freescale.com

For Literature Requests Only:
Freescale Semiconductor Literature Distribution Center
P.O. Box 5405
Denver, Colorado 80217
1-800-441-2447 or 303-675-2140
Fax: 303-675-2150
LDCForFreescaleSemiconductor@hibbertgroup.com

Information in this document is provided solely to enable system and software implementers to use Freescale Semiconductor products. There are no express or implied copyright licenses granted hereunder to design or fabricate any integrated circuits or integrated circuits based on the information in this document.

Freescale Semiconductor reserves the right to make changes without further notice to any products herein. Freescale Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Freescale Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters that may be provided in Freescale Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals", must be validated for each customer application by customer's technical experts. Freescale Semiconductor does not convey any license under its patent rights nor the rights of others. Freescale Semiconductor products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Freescale Semiconductor product could create a situation where personal injury or death may occur. Should Buyer purchase or use Freescale Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold Freescale Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Freescale Semiconductor was negligent regarding the design or manufacture of the part.

Freescale™ and the Freescale logo are trademarks of Freescale Semiconductor, Inc. All other product or service names are the property of their respective owners.
© Freescale Semiconductor, Inc. 2006. All rights reserved.

